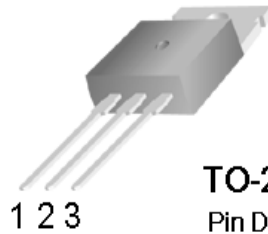


## High Voltage NPN Power Transistor

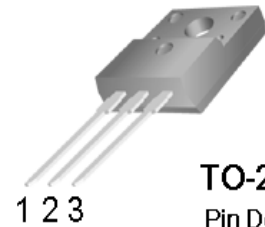
### Features

- High Voltage
- High Switch Speed
- $BV_{CEO} : 400V$
- $BV_{CBO} : 700V$
- $I_C : 3A$
- $V_{CE(SAT)} : 2V @ I_C / I_B = 2A / 0.5A$



#### TO-220

- Pin Definition
1. Base
  2. Collector
  3. Emitter



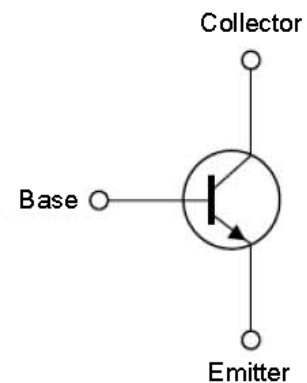
#### TO-220F

- Pin Definition
1. Base
  2. Collector
  3. Emitter

### Application

- Electronic Ballasts
- Adapter
- Lighting

### INTERNAL SCHMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^{\circ}C$ )

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	$V_{CBO}$	700	V
Collector-Emitter Voltage	$V_{CEO}$	400	V
Collect-Break Down Voltage	$V_{CES}$	700	V
Emitter-Base Voltage	$V_{EBO}$	9	V
Total Power Dissipation @ $T_c \leq 25^{\circ}C$ / TO-220	$P_{tot}$	60	W
Total Power Dissipation @ $T_c \leq 25^{\circ}C$ / TO-220F	$P_{tot}$	28	W
Collector Peak Current ( $t_p < 5ms$ )	$I_{CM}$	6	A
Collector Current	$I_C$	3	A
Base Peak Current ( $t_p < 5ms$ )	$I_{BM}$	3	A
Base Current	$I_B$	1.5	A
Maximum Operating Junction Temperature	$T_J$	+150	$^{\circ}C$
Operating Junction and Storage Temperature Range	$T_{STG}$	-65 ~ +150	$^{\circ}C$

Note: Single Pulse.  $P_w=300\mu S$ , Duty  $\leq 2\%$

**ELECTRICAL SPECIFICATIONS**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Voltage	BVCBO	IC = 10mA, IB=0	700	–	–	V
Collector-Emitter Breakdown Voltage	BVCEO	IC = 10mA, IE=0	400	–	–	V
Emitter- Base Breakdown Voltage	BVEBO	IE = 1mA, IC=0	9	–	–	V
Collector Cutoff Current	ICBO	VCB = 700V, IE=0	–	–	100	uA
Emitter Cutoff Current	IEBO	VEB = 9V, IC=0	–	–	10	uA
DC Current Gain	hFE1	VCE = 5V, IC=10mA	10	27	–	
	hFE2	VCE = 5V, IC=1A	10	–	30	
	hFE3	VCE = 5V, IC=2A	4	–	24	
Collector-Emitter Saturation Voltage	VCE(SAT1)	IC = 0.5A, IB =0.1A	–	–	0.5	V
	VCE(SAT2)	IC = 0.6A, IB =60mA	–	–	0.7	
	VCE(SAT3)	IC = 2A, IB =0.5A	–	1.5	2	
Frequency	f <sub>f</sub>	VCE = 10V, IC=0.1A	4	–	–	MHz
Output Capacitance	Cob	VCB = 10V, IC=0.1MHz	–	21	–	pF
Turn On Time	t <sub>on</sub>	Vcc = 125V, Ic = 1A, IB1=1B2=0.2A, RL=125ohm	–	0.4	–	uS
Storage Time	t <sub>STG</sub>		–	2.0	–	uS
Fall Time	t <sub>f</sub>		–	0.16	–	uS

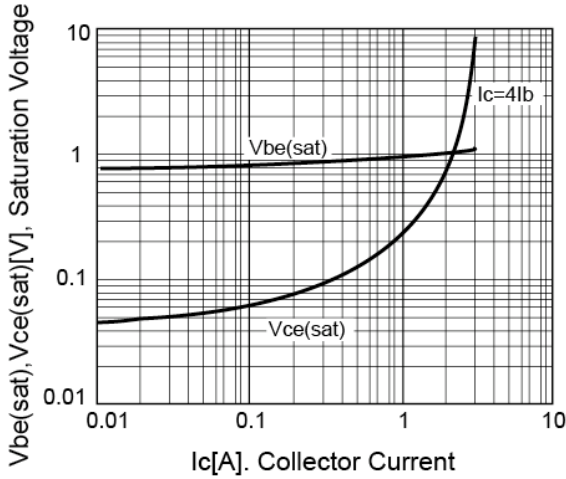
Note: Pulse test: pulse width  $\leq$  300uS, duty cycle  $\leq$  2%

**Thermal Performance**

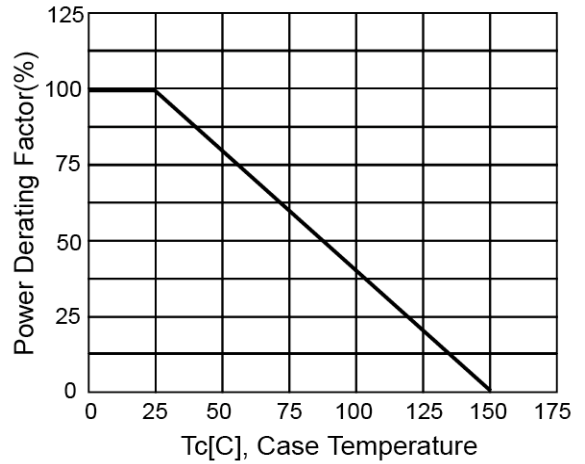
Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance TO-220	R $\theta_{JC}$	2.08	°C/W
Junction to Case Thermal Resistance TO-220F	R $\theta_{JC}$	4.46	°C/W

**Electrical Characteristics Curve** ( $T_a = 25^\circ\text{C}$ , unless otherwise noted)

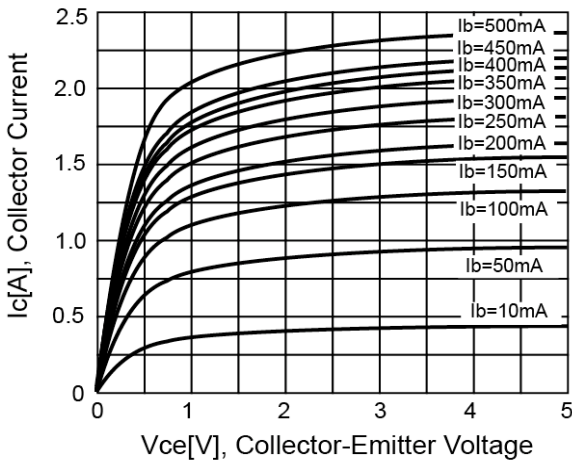
**$V_{CE(SAT)}$  V.S.  $V_{BE(SAT)}$**



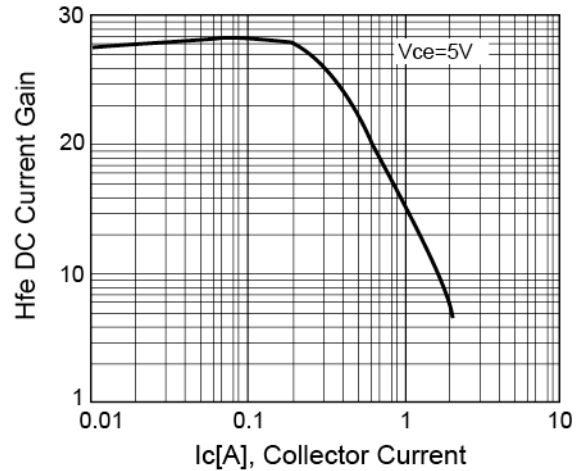
**Power Derating**



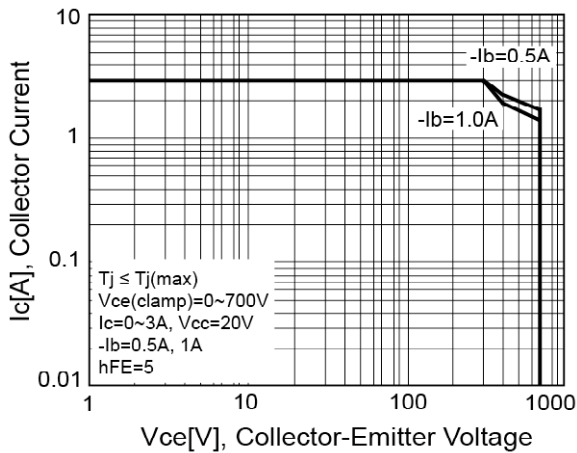
**Static Characteristics**



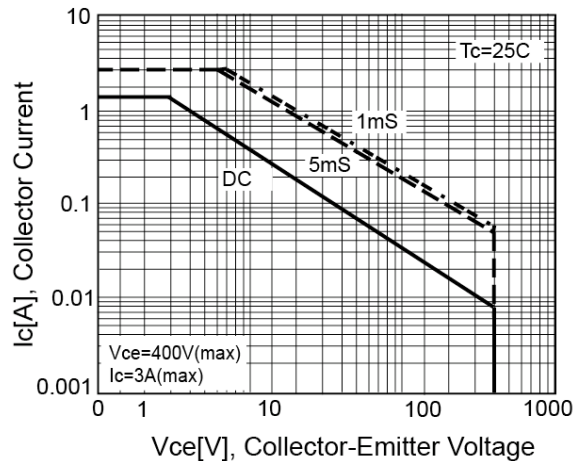
**DC Current Gain**



**Reverse Bias SOA**



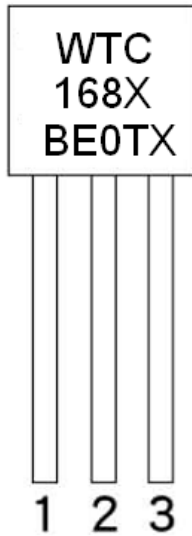
**Safety Operating Area**



### Ordering Information

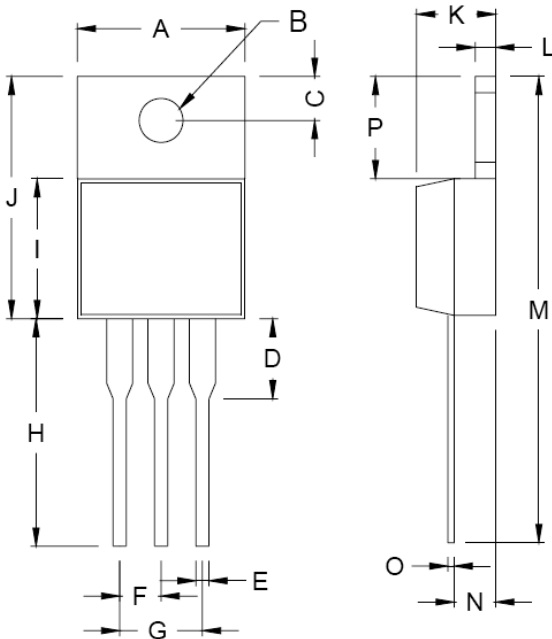
Type NO	Marking	Package Code
WTX168	168X	TO-220

### Marking and Pin Define



First Line	WTC	Company Name	
Second Line	168X	Product Code	
Third Line	BE0TX	1st (Year Code)	A-2010 B-2011 C-2012 ...
		2nd (Month Code)	A-Jan, B-Feb, C-Mar, D-Apr, E-May, F-Jun, G-Jul, H-Aug, I-Sep, J-Oct, K-Nov, L-Dec
		3rd (Lot Code)	0~1, A~9
		4th (Product Code)	M-MOS, T-Transistor
		5th (Package Code)	I-T0251, D-T0252, L-T092, M-T0126, X-T0220
		6th (Spec Code)	(Reserve)

### TO-220 Package Dimension

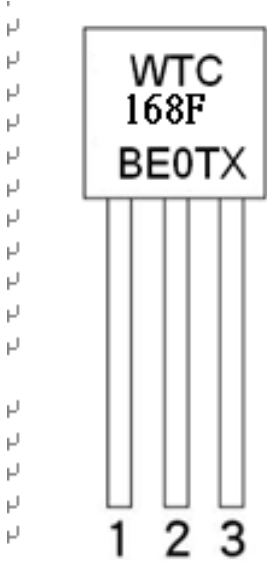


DIM	TO-220 DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	10.000	10.500	0.394	0.413
B	3.740	3.910	0.147	0.154
C	2.440	2.940	0.096	0.116
D	-	6.350	-	0.250
E	0.75	0.85	0.029	0.033
F	2.345	2.715	0.092	0.058
G	4.690	5.430	0.092	0.107
H	12.700	14.732	0.500	0.581
J	14.224	16.510	0.560	0.650
K	3.556	4.826	0.140	0.190
L	1.285	1.315	0.050	0.051
M	27.700	29.620	1.060	1.230
N	2.032	2.921	0.080	0.115
O	0.255	0.610	0.010	0.024
P	5.842	6.858	0.230	0.270

### Ordering Information

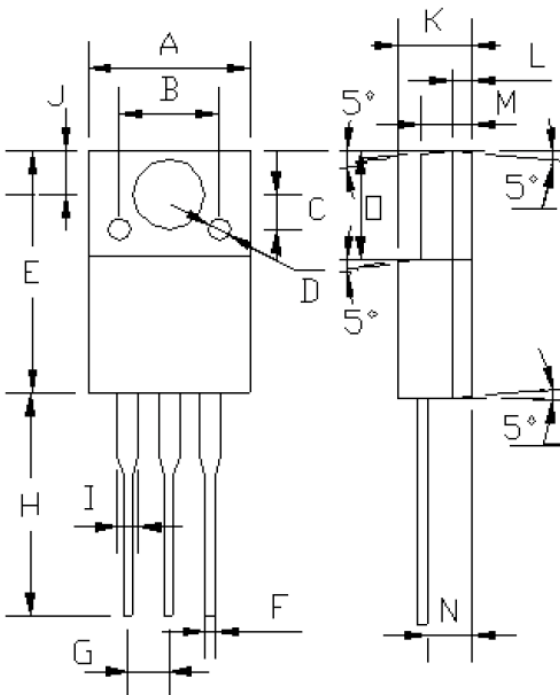
Type NO	Marking	Package Code
WTF168	168F	TO-220F

### Marking and Pin Define



First Line	WTC	Company Name	
Second Line	168F	Product Code	
Third Line	BE0TX	1st (Year Code)	A-2010 B-2011 C-2012 ...
		2nd (Month Code)	A-Jan, B-Feb, C-Mar, D-Apr, E-May, F-Jun, G-Jul, H-Aug, I-Sep, J-Oct, K-Nov, L-Dec
		3rd (Lot Code)	0-1, A-9
		4th (Product Code)	M-MOS, T-Transistor
		5th (Package Code)	I-T0251, D-T0252, L-T092, M-T0126, X-T0220
		6th (Spec Code)	(Reserve)

### TO-220F Package Dimension



DIM	220F DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.96	10.36	0.392	0.407
B	6.20 (typ.)		0.244 (typ.)	
C	2.20 (typ.)		0.087 (typ.)	
D	1.40 (typ.)		0.055 (typ.)	
E	15.07	16.07	0.593	0.632
F	0.80 (typ.)		0.031 (typ.)	
G	2.44	2.64	0.096	0.104
H	13.08	13.48	0.514	0.530
I	1.47 (max.)		0.057 (max.)	
J	3.20	3.40	0.125	0.133
K	4.60	4.80	0.181	0.188
L	1.15 (typ.)		0.045 (typ.)	
M	2.44	2.64	0.096	0.104
N	2.60	2.80	0.102	0.110
O	6.55	6.65	0.258	0.262